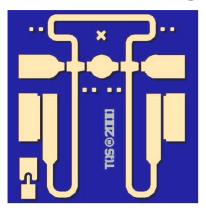


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Wideband Dual Stage VPIN Limiter

TGL2201-EPU



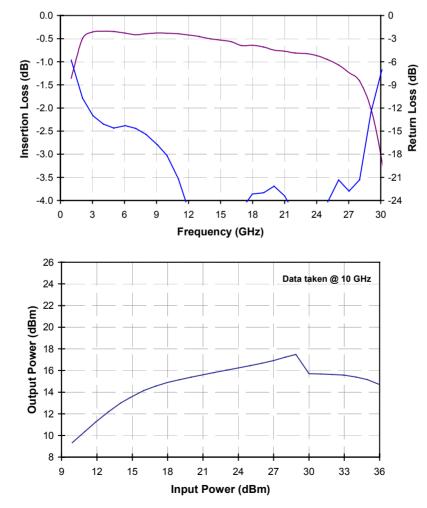
Key Features

- 3-25 GHz Passive, High Isolation Limiter
- Low Loss < 0.5 dB , X-band
- Good Return Loss > 15 dB
- Flat Leakage < 18 dBm
- Input Power CW Survivability > 5W
- Integrated DC Block on both input and output
- Chip Dimensions: 1.1 x 1.1 x 0.1 mm

Primary Applications

- Military Radar
- LNA Receiver Chain Protection

Fixtured Measured Performance



Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.



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TABLE I MAXIMUM RATINGS

Symbol	Parameter 1/	Value
P _{IN}	Input Continuous Wave Power	37 dBm
T _M	Mounting Temperature (30 Seconds)	320 ⁰ C
T _{STG}	Storage Temperature	-65 to 150 ⁰ C

<u>1</u>/ These ratings represent the maximum operable values for this device

TABLE II DC CHARACTERISTICS $(T_A = 25 \ ^{\circ}C)$

Symbol	Parameter	L	Limit	
		Min	Max	-
FWD_RES (D1, D2, D3, D4)	Resistance Forward	1.9	3.9	Ohm
VREV _(D1,D4)	Reverse Voltage	-60	-30	V

TABLE III RF CHARACTERISTICS $(T_A = 25 \text{ °C})$

Symbol	Parameter	Test Condition	Limit		Units	
•			Min	Тур	Max	
IL	Insertion Loss	F = 4-20 GHz		0.5	1.0	dB
IRL	Input Return Loss	F = 4-20 GHz	12			dB
ORL	Output Return Loss	F = 4-20 GHz	12			dB
PWR	Output Power @	F = 6.0 GHz			20	dBm
	$P_{in} = 27 \text{ dBm}$	F = 16.0 GHz			20	dBm

Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.

2

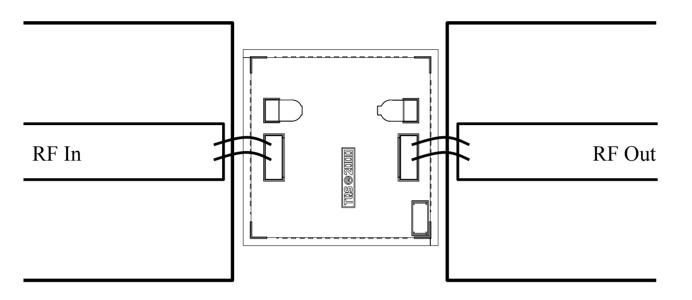


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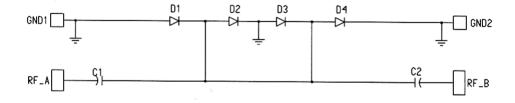
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3

High Isolation Limiter Assembly



DC Schematic



Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.

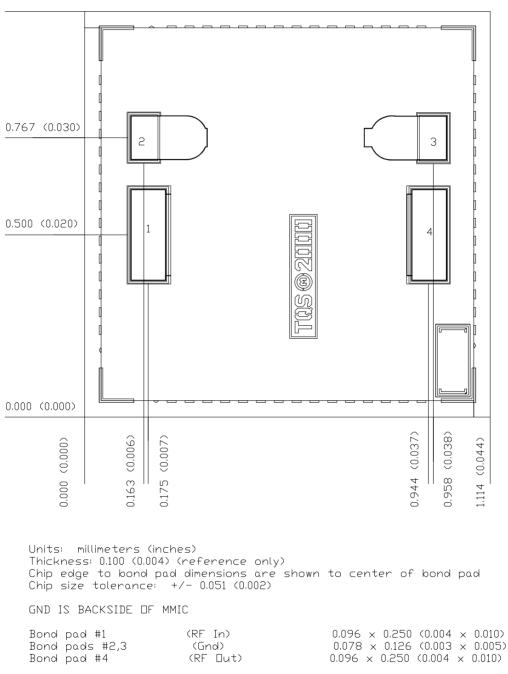


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Mechanical Drawing

1.114 (0.044)



GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

Note: Devices designated as EPU are typically early in their characterization process prior to finalizing all electrical and process specifications. Specifications are subject to change without notice.

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Assembly Process Notes

Reflow process assembly notes:

- Use AuSn (80/20) solder with limited exposure to temperatures at or above 300 °C for 30 sec
- An alloy station or conveyor furnace with reducing atmosphere should be used.
- No fluxes should be utilized.
- Coefficient of thermal expansion matching is critical for long-term reliability.
- Devices must be stored in a dry nitrogen atmosphere.

Component placement and adhesive attachment assembly notes:

- Vacuum pencils and/or vacuum collets are the preferred method of pick up.
- Air bridges must be avoided during placement.
- The force impact is critical during auto placement.
- Organic attachment can be used in low-power applications.
- Curing should be done in a convection oven; proper exhaust is a safety concern.
- Microwave or radiant curing should not be used because of differential heating.
- Coefficient of thermal expansion matching is critical.

Interconnect process assembly notes:

- Thermosonic ball bonding is the preferred interconnect technique.
- Force, time, and ultrasonics are critical parameters.
- Aluminum wire should not be used.
- Maximum stage temperature is 200 °C.

GaAs MMIC devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

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